



SS56L Schottky Barrier Diode

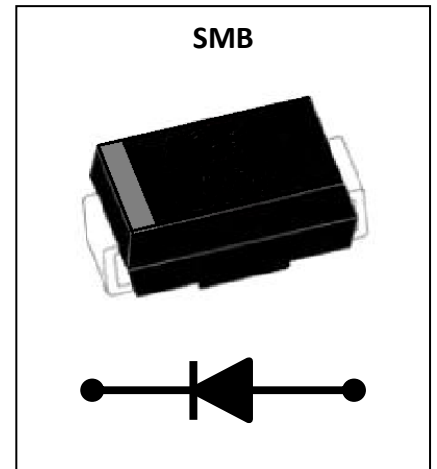
Feature

- High current capability
- Low VF, Low IR
- High Junction Temperature
- High surge current capability

Application

- Rectifier

MARKING



ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

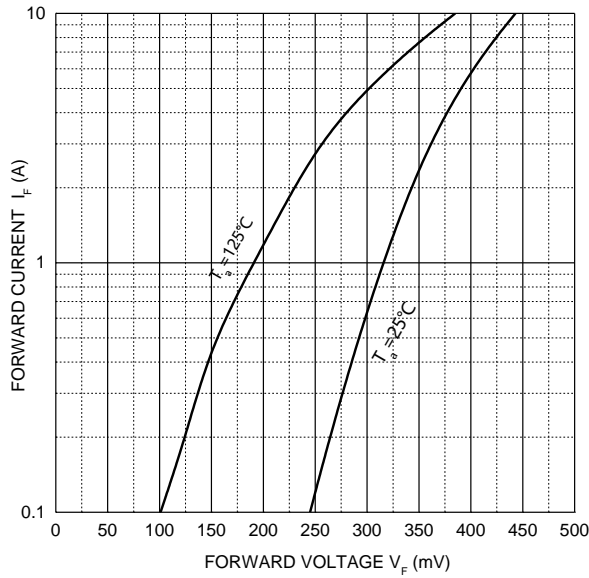
Parameter	Symbol	Value	Unit
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	60	V
Mean rectifying current	I _O	5.0	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	150	A
Maximum Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

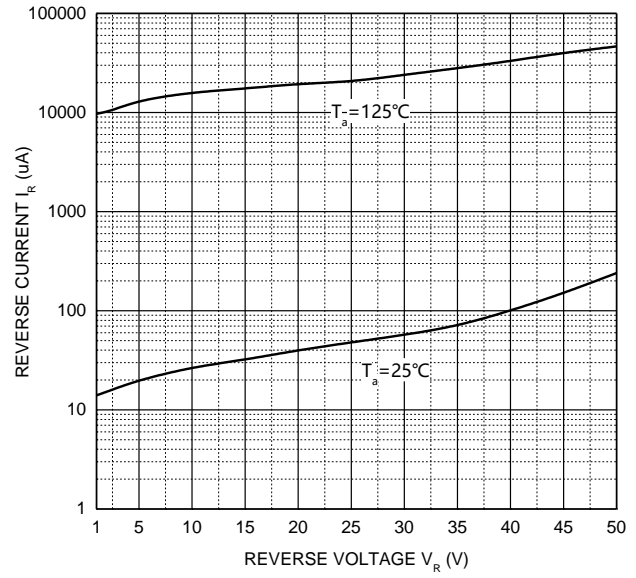
Parameter	Symbol	Test Condition	Min	Typical	Max	Unit
Reverse voltage	V _{BR}	I _R =250μA	60	65		V
		I _F =2A		0.42	0.46	V
		I _F =3A		0.44	0.48	V
		I _F =5A		0.46	0.52	V
Reverse current	I _R	V _R =60V		50	300	μA
		V _R =60V, T _a =100°C			15	mA
Typical Thermal Resistance	R _{θJ-A}	Between junction and ambient	45			°C/W
	R _{θJ-L}	Between junction and lead	8			°C/W
Typical Junction Capacitance	C _J	V _R =4V, f=1MHz	500			pF

Typical Characteristics

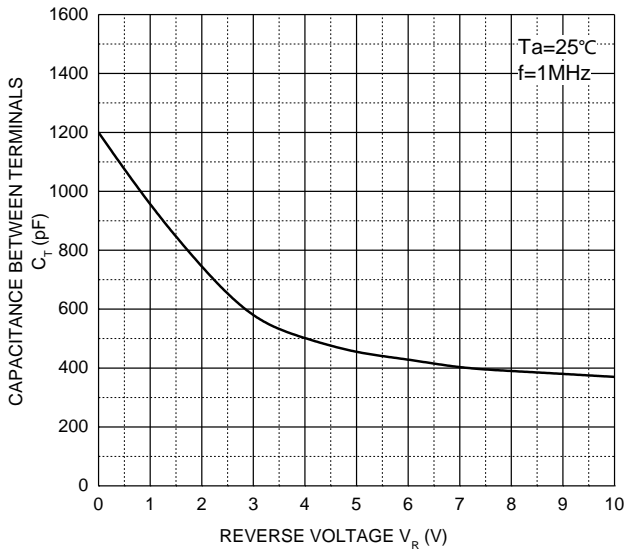
Forward Characteristics



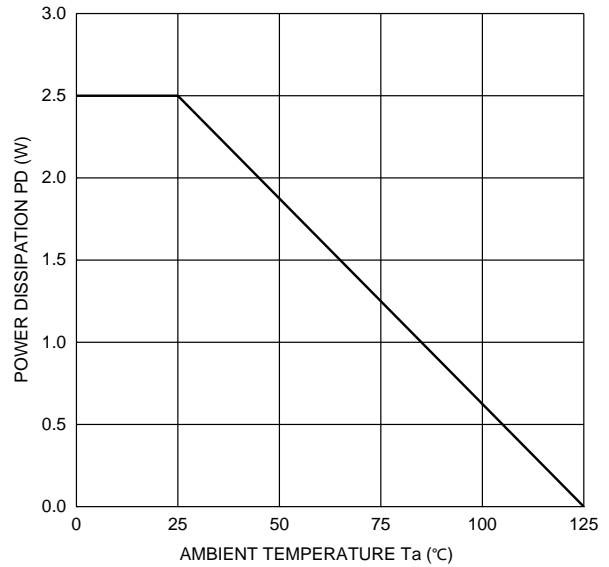
Reverse Characteristics



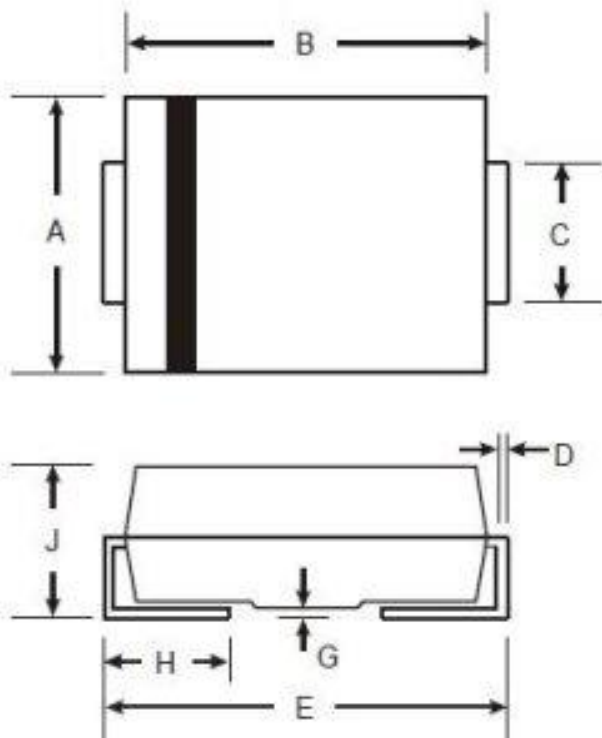
Capacitance Characteristics



Power Derating Curve



SMB Package Outline Dimensions



SMB		
Dim	Min	Max
A	3.30	3.94
B	4.06	4.57
C	1.96	2.21
D	0.15	0.31
E	5.00	5.59
G	0.05	0.20
H	0.76	1.52
J	2.00	2.50
All Dimensions in mm		

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)